COMPLIANT

HALOGEN

FREE





2 Port, USB 2.0 High Speed (480 Mbps) Switch, **DPDT** Analog Switch

DESCRIPTION

The DG2722 is 2 port high speed analog switch optimized for USB 2.0 signal switching. The DG2722 switch is configured in DPDT. It handles bidirectional signal flow, achieving a 900 MHz - 3 dB bandwidth, and a port to port crosstalk and isolation at - 49 dB.

Processed with high density sub micron CMOS, the DG2722 provide low parasitic capacitance. Signals are routed with minimized phase distortion and attain a bit to bit skew is as low as 40 pS.

The DG2722 is designed for a wide range of operating voltages, from 2.7 V to 4.3 V that can be driven directly from one cell Li-ion battery. On-chip circuitry protects against conditions when either the D+/D- lines are shorted to the V_{BLIS} at the USB port. Additionally, logic control pins (S and OE) can tolerate the presence of voltages that are above the supply power rail (V+). The control logic threshold is guaranteed to be $(V_{IH} = 1.3 \text{ V/min})$. Latch up current is 300 mA, as per JESD78, and its ESD tolerance exceeds 8 kV.

Packaged in ultra small miniQFN-10 (1.4 mm x 1.8 mm x 0.55 mm), it is ideal for portable high speed mix signal switching application.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with lead (Pb)-free device termination. The miniQFN-10 package has a nickel-palladium-gold device termination and is represented by the lead (Pb)-free "-E4" suffix to the ordering part number. The nickel-palladium-gold device terminations meet all JEDEC standards for reflow and MSL rating.

As a further sign of Vishay Siliconix's commitment, the DG2722 is fully RoHS complaint.

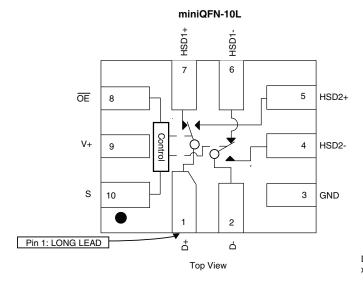
FEATURES

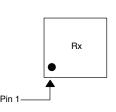
- Halogen-free according to IEC 61249-2-21 **Definition**
- Wide operation voltage range
- Low on-resistance, 7 Ω (typical at 3 V)
- Low capacitance, $C_{ON} = 5.8 \text{ pF (typical)}$
- 3 dB high bandwidth: 900 MHz (typical)
- Low bit to bit skew: 40 pS (typical)
- Low power consumption
- Low logic threshold: V
- Power down protection: D+/D- pins can tolerate up to 5 V when V+=0 V
- Logic (S and OE) above V+ tolerance
- 8 kV ESD protection (HBM)
- Latch-up current 300 mA per JESD78
- Lead (Pb)-free low profile miniQFN-10 (1.4 mm x 1.8 mm x 0.55 mm)
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

- Cellular phones
- Portable media players
- Digital camera
- **GPS**
- Notebook computer
- TV, monitor, and set top box

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION





Device marking: Rx for DG2722 x = Date/Lot Traceability Code

Document Number: 68379 S11-2216-Rev. F, 14-Nov-11 www.vishav.com



ORDERING INFORMAT	ORDERING INFORMATION				
Temp. Range	Package	Part Number			
- 40 °C to 85 °C	miniQFN-10	DG2722DN-T1-E4			

TRUTH T	H TABLE						
OE (Pin 8)	S (Pin 10)	Function					
0	0	D+ = HSD1+ and D- = HSD1-					
0	1	D+ = HSD2+ and D- = HSD2-					
1	Х	Disconnect					

PIN DESCRIPTIONS				
Pin Name	Description			
ŌĒ	Bus Switch Enable			
S	Select Input			
HSD1±, HSD2±, D±	Data Port			

ABSOLUTE MAXIMUM RAT	INGS (T _A = 25 °C, unless otherwis	se noted)		
Parameter		Limit	Unit	
Reference to GND	V+	- 0.3 to 5	V	
helerence to GIND	S, OE, D±, HSD1±, HSD2±a	- 0.3 to (V+ + 0.3)		
Current (Any Terminal except S, OE, D±, HSD1±, HSD2±)		30		
Continuous Current (S, OE, D±, HSD1±, HSD2±)		± 250	mA	
Peak Current (Pulsed at 1 ms, 10 % Duty Cycle)		± 500		
Storage Temperature (D Suffix)		- 65 to 150	°C	
Power Dissipation (Packages) ^b miniQFN-10 ^c		208	mW	
ESD (Human Body Model) I/O to GND		8	kV	
Latch-up (Current Injection)		300	mA	

Notes:

- a. Signals on S, $\overline{\text{OE}}$, D±, HSD1±, HSD2± exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current
- b. All leads welded or soldered to PC board.
- c. Derate 2.6 mW/°C above 70 °C.

SPECIFICATIONS (V+ = 3 V)							
		Test Conditions		Limits - 40 °C to 85 °C			
Parameter	Symbol	Otherwise Unless Specified	Temp.a	Min.b	Typ.c	Max.b	Unit
Analog Switch							
Analog Signal Range ^d	V _{ANALOG}	R _{DS(on)}	Full	0		V+	V
On-Resistance	R	$V+ = 3 \text{ V}, I_{D+} = 8 \text{ mA}, V_{\text{HSD1/2+}} = 0.4 \text{ V}$	Room		7	8	
On-nesistance	R _{DS(on)}	$v + = 3 v$, $i_{D\pm} = 0 \text{ IIIA}$, $v_{HSD1/2\pm} = 0.4 v$	Full			9	
On-Resistance Match ^d	ΔR_{ON}	$V+ = 3 \text{ V}, I_{D\pm} = 8 \text{ mA}, V_{HSD1/2\pm} = 0.4 \text{ V}$	Room		0.8		Ω
On-Resistance Resistance Flatness ^d	R _{ON} Flatness	$V+=3 \text{ V}, I_{D\pm}=8 \text{ mA}, V_{HSD1/2\pm}=0 \text{ V}, 1 \text{ V}$	Room		2		
Switch Off Leakage Current	I _(off)	$V+ = 4.3 \text{ V}, V_{HSD1/2\pm} = 0.3 \text{ V}, 3 \text{ V}, $ $V_{D\pm} = 3 \text{ V}, 0.3 \text{ V}$	Full	- 100		100	^
Channel On Leakage Current	I _(on)	$V+ = 4.3 \text{ V}, V_{\text{HSD1/2\pm}} = 0.3 \text{ V}, 4 \text{ V}, $ $V_{\text{D\pm}} = 4 \text{ V}, 0.3 \text{ V}$	Full	- 200		200	nA
Digital Control							
Innut Valtage Lligh	V	V+ = 3 V to 3.6 V	Full 1.3				
Input Voltage High	V _{INH}	V+ = 4.3 V	Full	1.5			٧
Input Voltage Low	V_{INL}	V+ = 3 V to 4.3 V	Full			0.5	1
Input Capacitance	C _{IN}		Full		6.5		pF
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	- 1		1	μΑ



SPECIFICATIONS (V+=	= 3 V)						
		Test Conditions	Limits - 40 °C to 85 °C		5 °C		
Parameter	Symbol	Otherwise Unless Specified	Temp.a	Min.b	Typ.c	Max.b	Unit
Dynamic Characteristics							
Break-Before-Make Time ^{e, d}	t _{BBM}		Room		5		
		V: 0 V V	Room				
S, OE Turn-On Time ^{e, d}	t_{ON}	V+ = 3 V, $V_{D1/2 \pm} = 1.5 V$, $R_L = 50 Ω$, $C_1 = 35 pF$	Full			30	ns
		ου = 00 βι	Room				
S, OE Turn-Off Time ^{e, d}	t_{OFF}		Full			25	
Charge Injection ^d	Q _{INJ}	$C_L = 1 \text{ nF, } R_{GEN} = 0 \Omega, V_{GEN} = 0 V$			0.5		рС
Off-Isolation ^d	OIRR	$V+ = 3 V \text{ to } 3.6 V, R_1 = 50 \Omega, C_1 = 5 pF,$			- 30		40
Crosstalk ^d	X _{TALK}	f = 240 MHz			- 45		dB
Bandwidth ^d	BW	V+ = 3 V to 3.6 V, R_L = 50 Ω , - 3 dB			900		MHz
D+/D- On Capacitance	C _{ON}	V+ = 3.3 V, OE = 0 V, f = 240 MHz	Room		5.8		,r
D1n, D2n Off Capacitance	C _{OFF}	$V + = \overline{OE} = 3.3 \text{ V, f} = 240 \text{ MHz}$	1100111		2.2		pF
Channel-to-Channel Skew ^d	t _{SK(O)}		1		50		
Skew Off Opposite Transitions of the Same Output ^d	t _{SK(p)}	V+ = 3 V to 3.6 V, R_L = 50 Ω, C_L = 5 pF			20		ps
Total Jitter ^d	tر				200		
Power Supply							
Power Supply Range	V+			2.6		4.3	V
Power Supply Current	l+	$V_{IN} = 0 V, \text{ or } V+$	Full			2	μΑ

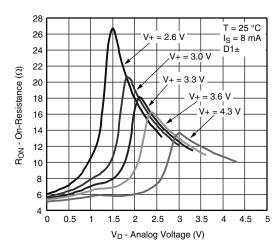
Notes:

- a. Room = 25 °C, Full = as determined by the operating suffix.
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
- c. Typical values are for design aid only, not guaranteed nor subject to production testing.
- d. Guarantee by design, not subjected to production test.
- e. V_{IN} = input voltage to perform proper function.
- f. Crosstalk measured between channels.

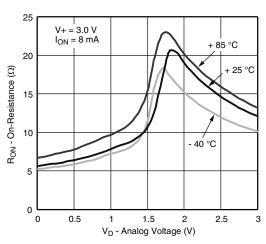
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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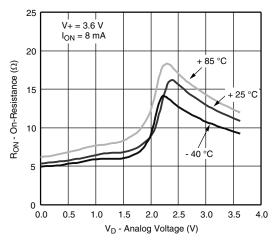
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



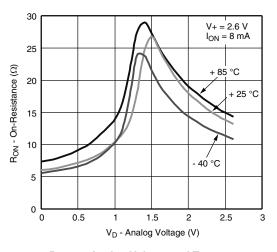
 R_{ON} vs. V_{D} and Single Supply Voltage



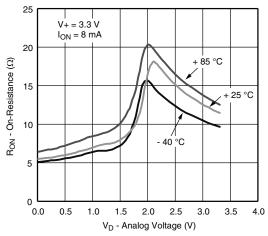
R_{ON} vs. Analog Voltage and Temperature



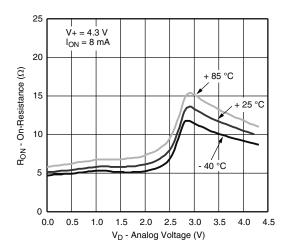
R_{ON} vs. Analog Voltage and Temperature



R_{ON} vs. Analog Voltage and Temperature



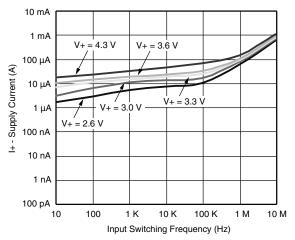
R_{ON} vs. Analog Voltage and Temperature



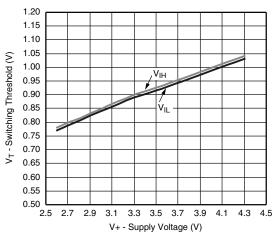
R_{ON} vs. Analog Voltage and Temperature



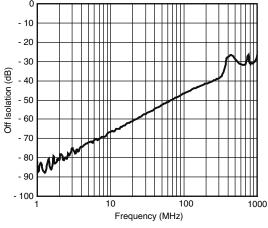
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



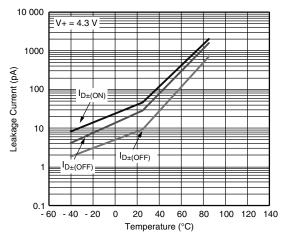
Supply Current vs. Input Switching Frequency



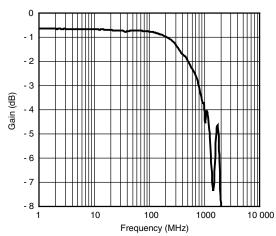
Switching Threshold vs. Supply Voltage



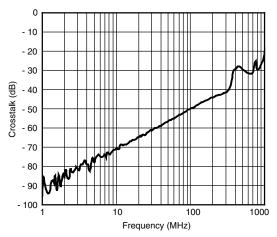
Off-Isolation, V+ = 3.3 V



Leakage Current vs. Temperature

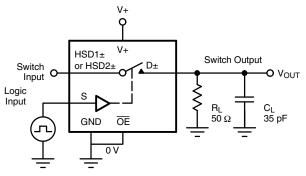


Gain vs. Frequency, V+ = 3.3 V



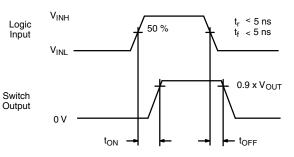
Crosstalk, V+ = 3.3 V

TEST CIRCUITS



C_L (includes fixture and stray capacitance)

$$V_{OUT} = D \pm \left(\frac{R_L}{R_L + R_{ON}} \right)$$



Logic "1" = Switch on Logic input waveforms inverted for switches that have the opposite logic sense.

Figure 1. Switching Time

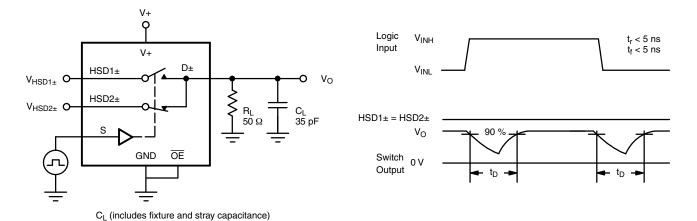


Figure 2. Break-Before-Make Interval

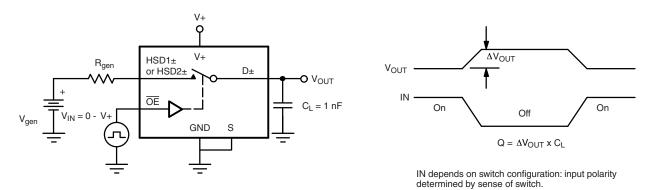


Figure 3. Charge Injection



TEST CIRCUITS

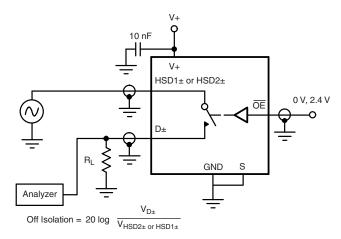


Figure 4. Off-Isolation

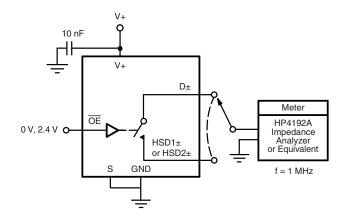
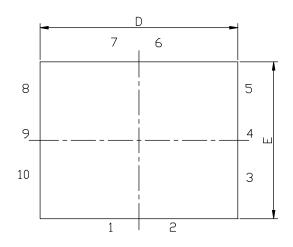
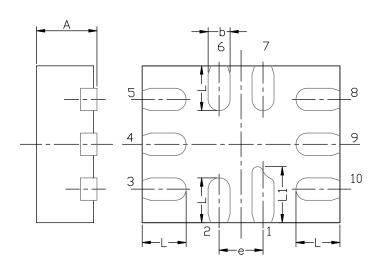


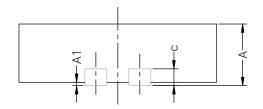
Figure 5. Channel Off/On Capacitance

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MINI QFN-10L CASE OUTLINE







DIM		MILLIMETERS		INCHES			
DIM	MIN.	NAM.	MAX.	MIN.	NAM.	MAX.	
Α	0.45	0.55	0.60	0.0177	0.0217	0.0236	
A1	0.00	-	0.05	0.000	-	0.002	
b	0.15	0.20	0.25	0.006	0.008	0.010	
С		0.150 or 0.127 REF ⁽¹⁾			0.006 or 0.005 REF ⁽¹⁾		
D	1.70	1.80	1.90	0.067	0.071	0.075	
Е	1.30	1.40	1.50	0.051	0.055	0.059	
е		0.40 BSC	0.016 BSC				
L	0.35	0.40	0.45	0.014	0.016	0.018	
L1	0.45	0.50	0.55	0.0177	0.0197	0.0217	

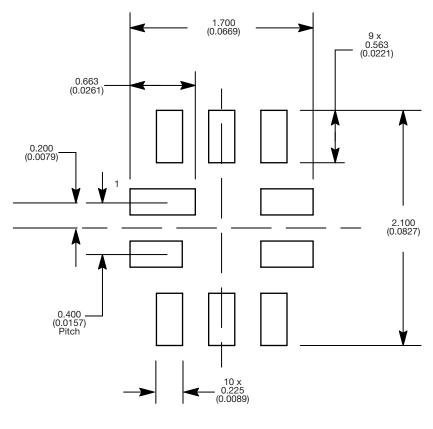
Note

ECN T16-0163-Rev. B, 16-May-16 DWG: 5957

⁽¹⁾ The dimension depends on the leadframe that assembly house used.



RECOMMENDED MINIMUM PADS FOR MINI QFN 10L



Mounting Footprint Dimensions in mm (inch)



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